



# Inductor-based switching converter for low voltage power distribution in LHC upgrades

S. Michelis, F. Faccio, A. Marchioro – PH/ESE/ME

1



# Working environment

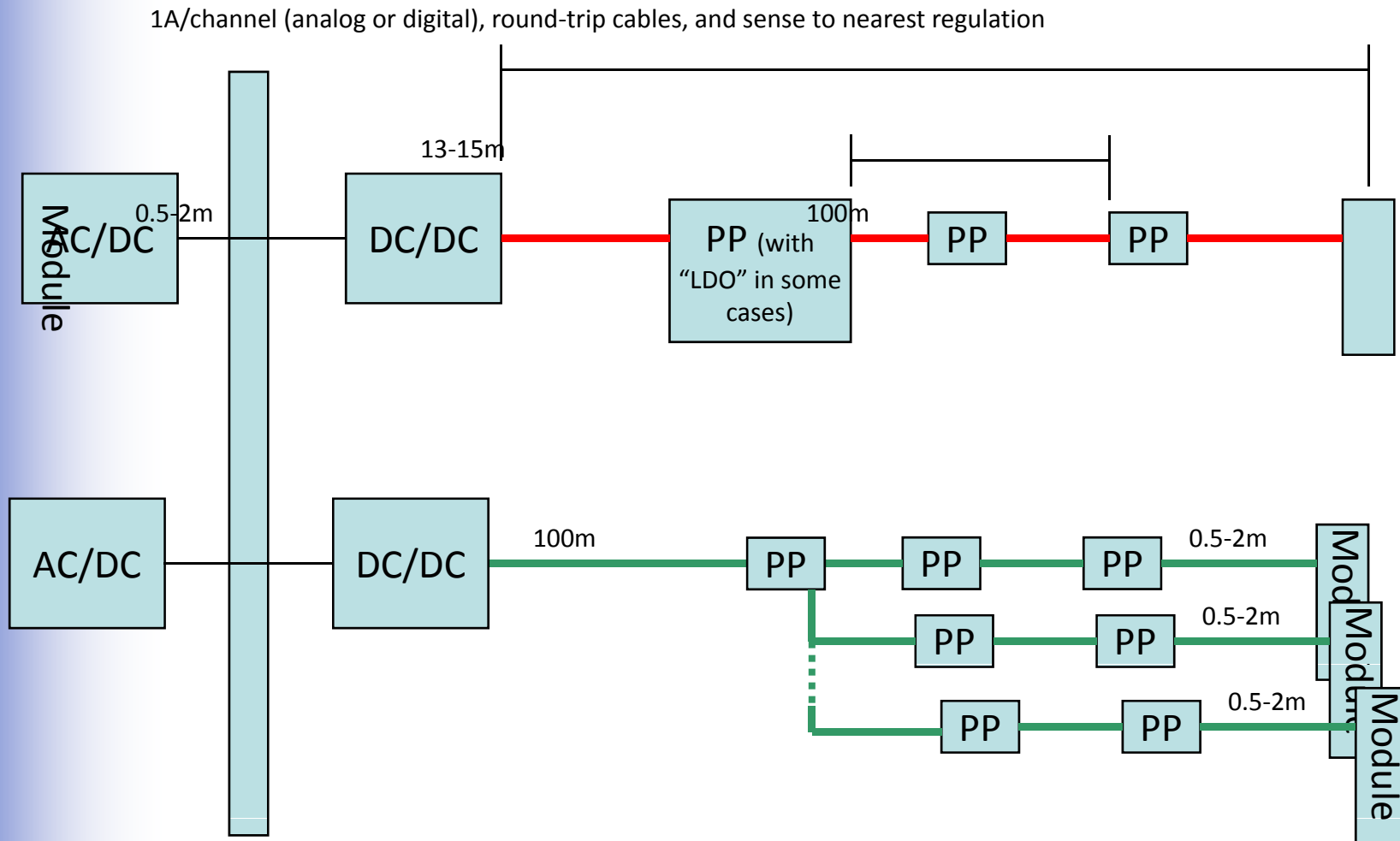
- ▶ **High magnetic field** (up to 4T in CMS, 2T in ATLAS)

- ▶ **High level of radiation** will be reached inside the detectors:

LHC doses probably increased x 5 – 10 so we can extrapolate to hundreds of Mrad in several Tracker location, decreasing to ten(s) in the outer Trackers

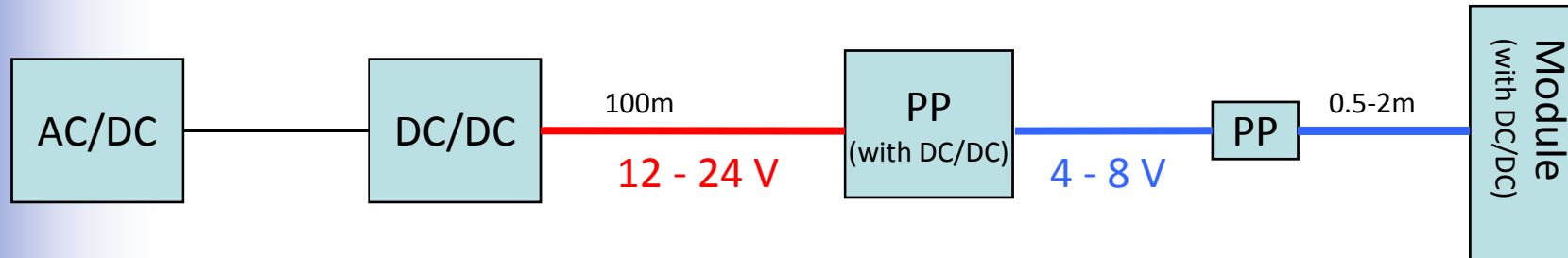


# Present power distribution schemes in trackers

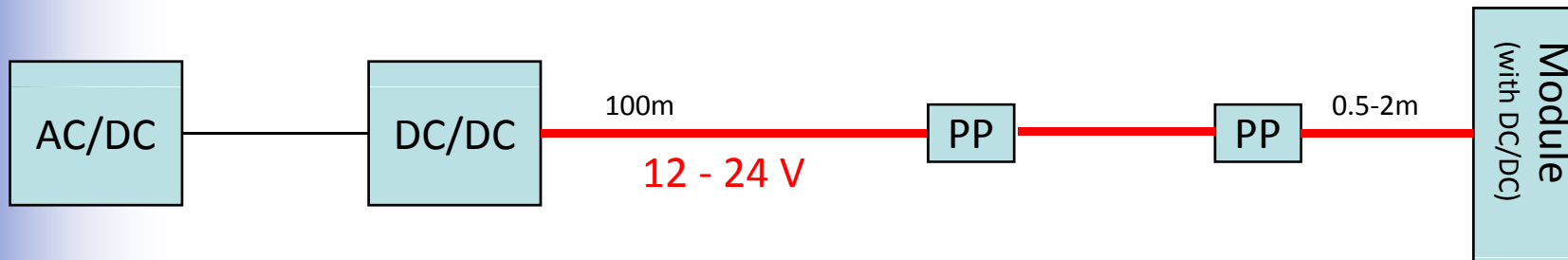




# Possible solutions

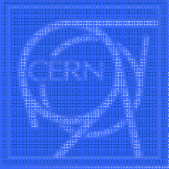


Same cables as today can bring more power,  
It requires efficient DC/DC on module for cooling



Small cables can bring all the power  
It requires efficient DC/DC

Important considerations:  
Magnetic field, Radiation  
and Material Budget, plus  
EMI if inductor-based DC/DC

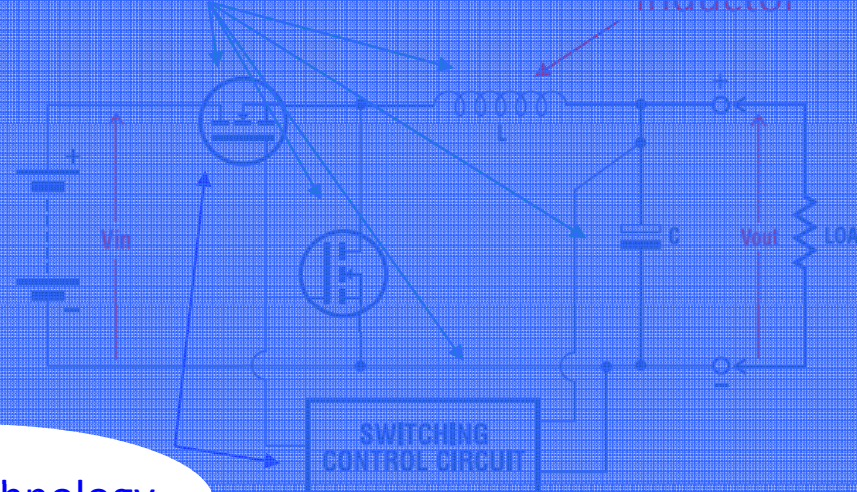


# DC-DC: Work in progress

- Aiming at demonstrating the feasibility of a fully integrated (except L and passive components) DC-DC buck converter

Power dissipation

Inductor



$V_{in}=12-24\text{ V}$   
 $V_{out}=1.5-3\text{ V}$   
 $I_{out}=1-2\text{ A}$

Rad-hard technology



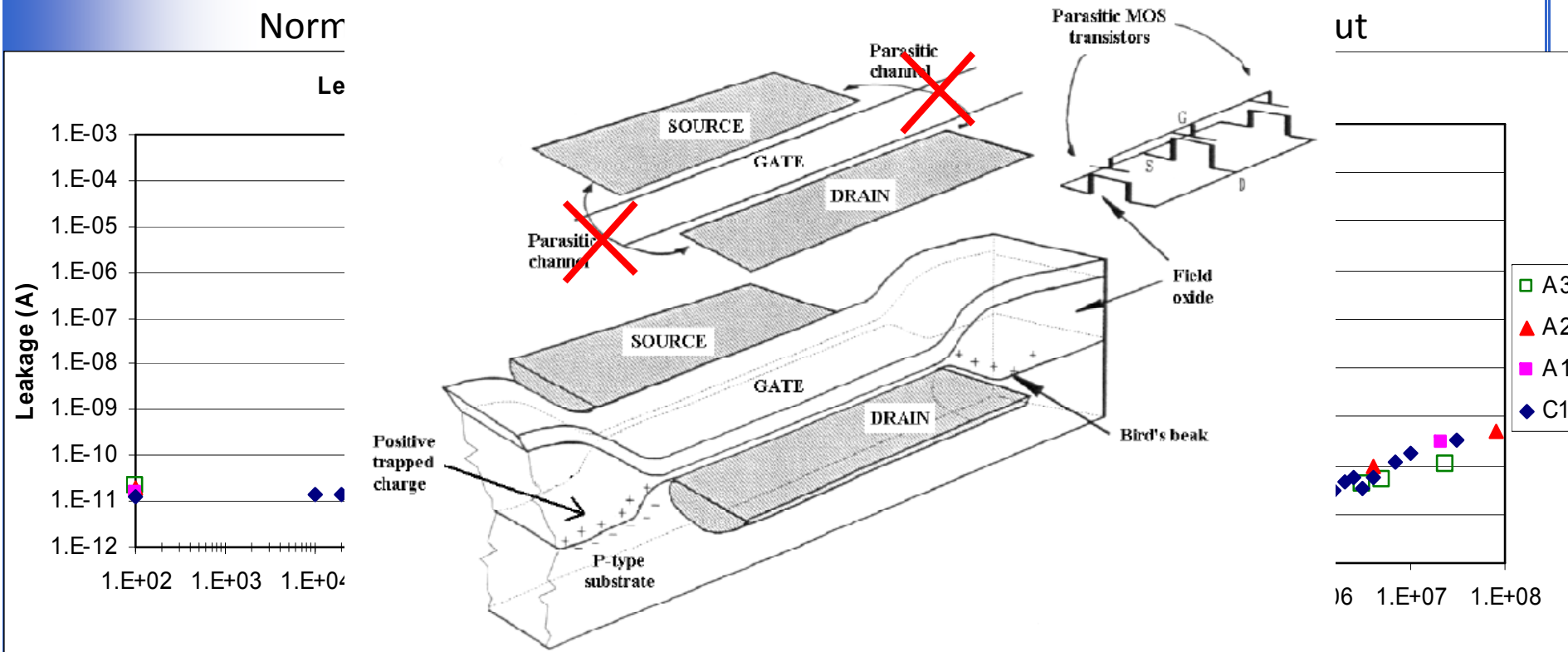
# Selection of a technology

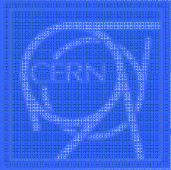
- Design and test of transistors of a 0.35  $\mu\text{m}$  technology usually employed in automotive application
- Several different transistor topologies available for high-V applications (lateral, vertical)
- It needs to be radiation tolerant



# Radiation Tolerant NMOS

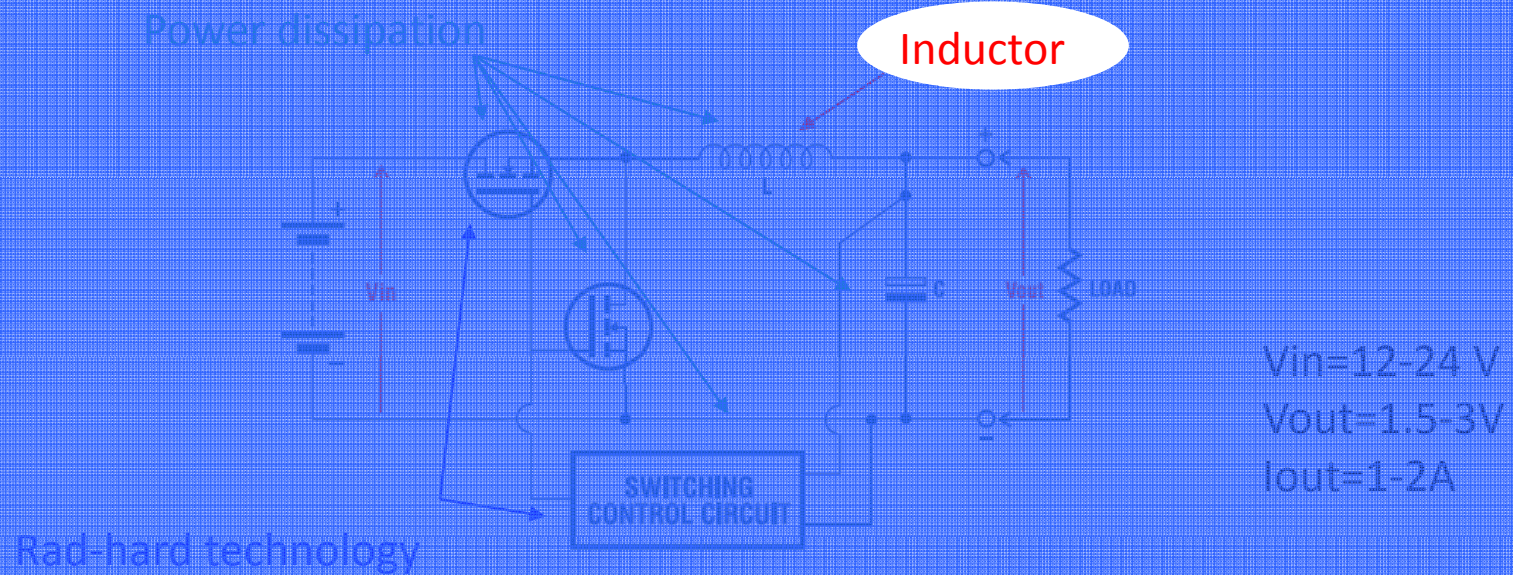
The main radiation-induced problem for the NMOS is the source-drain leakage current due to the radiation-induced trapping of positive charges in the thick lateral oxide  
 It is necessary to modify the layout of the NMOS in order to make them radiation tolerant.





# DC-DC: Work in progress

- Aiming at demonstrating the feasibility of a fully integrated (except L and passive components) DC-DC buck converter







# Inductors

- Inductor: need of air core inductor because of high magnetic field for CMS (up to 4 T) and ATLAS (up to 2 T)

Material	Initial Perm. $\mu$	B max (T)	Operating Frequencies
Fe	250	2,2	60-1000 Hz
Si-Fe (unoriented)	400	2,0	60-1000 Hz
Si-Fe (oriented)	1500	2,0	60-1000Hz
50-50 Ni Fe (grain-oriented)	2000	1,6	60-1000Hz
AMORPHOUS Alloy B	3000	1,5-1,6	to 250 kHz
High Flux powder	14 to 160	1,5	10 kHz to 1 MHz
Kool Mu <sup>®</sup> powder	26 to 125	1,0	to 10 MHz
Iron powder	5 to 80	1,0	100 kHz-100 MHz
79 Permalloy	12,000 to 100,000	8 to 1,1	1 kHz-75kHz
AMORPHOUS Alloy E	20,000	0.5-0.65	to 250 kHz
Ferrite-MnZn	750 To 15,000	0.3 to 0.5	10 kHz-2 MHz
Ferrite-NiZn	10 to 1500	0.3 to 0.5	200 kHz-100MHz
Permalloypowder	14 to 550	0.3	10 kHz-1 MHz

A Critical Comparison of Ferrites with other Magnetic Materials, 2000





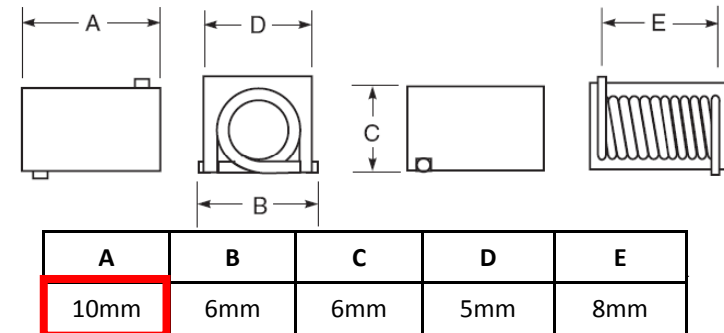
# Inductors

## Different commercial choices

### Coilcraft



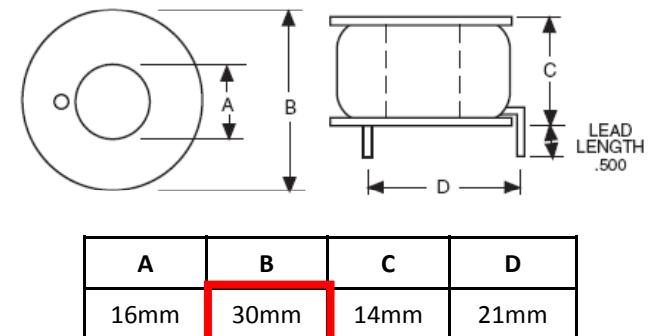
Inductance (nH)	DCR max (mOhm)	I <sub>rms</sub> (A)
380	50	2,5
538	90	2

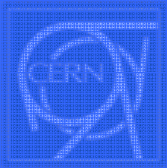


### Renco electronics



Inductance (nH)	DCR max (mOhm)	I <sub>rms</sub> (A)
560	6	8
1200	10	8

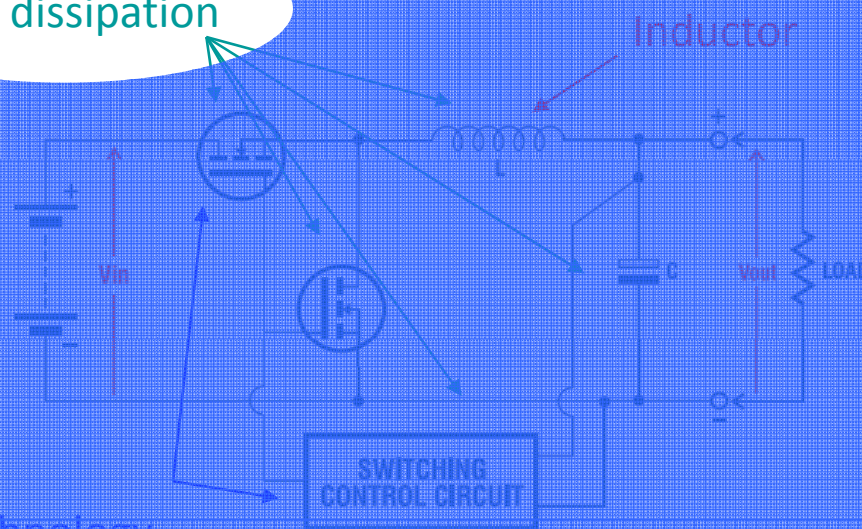




# DC-DC: Work in progress

- Aiming at demonstrating the feasibility of a fully integrated (except L and passive components) DC-DC buck converter

Power dissipation



Rad-hard technology

$V_{in}=12-24\text{ V}$   
 $V_{out}=1.5-3\text{ V}$   
 $I_{out}=1-2\text{ A}^1$



# Power losses

There are power losses in the circuit due to the non-ideal component.

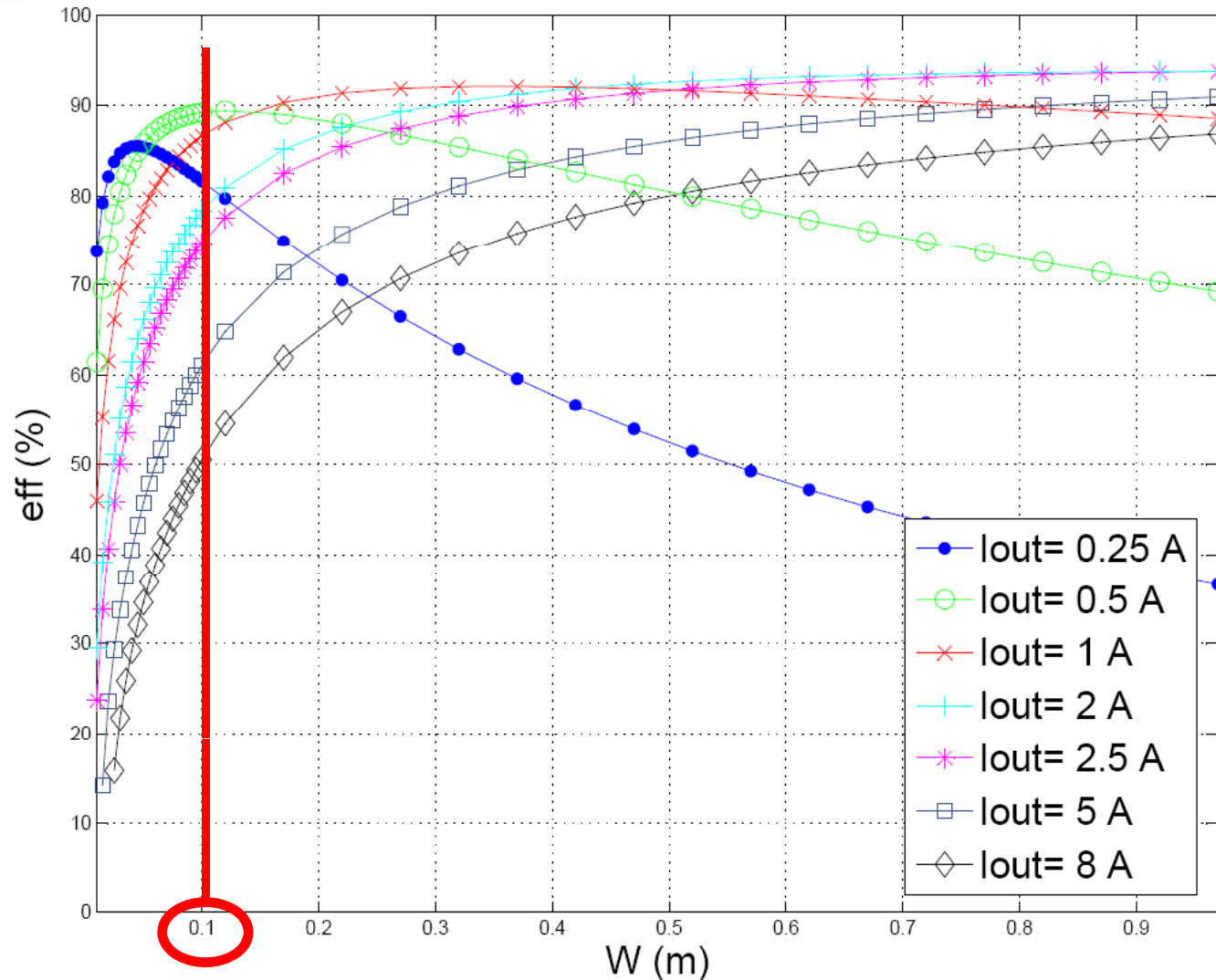
Mainly there are three losses that it is necessary to consider:

1. on  $R_{on}$  and  $R_{ind}$ , parasitic resistances of the switch and inductor, respectively;
2. on charging the gate capacitance;
3. on the control circuit.



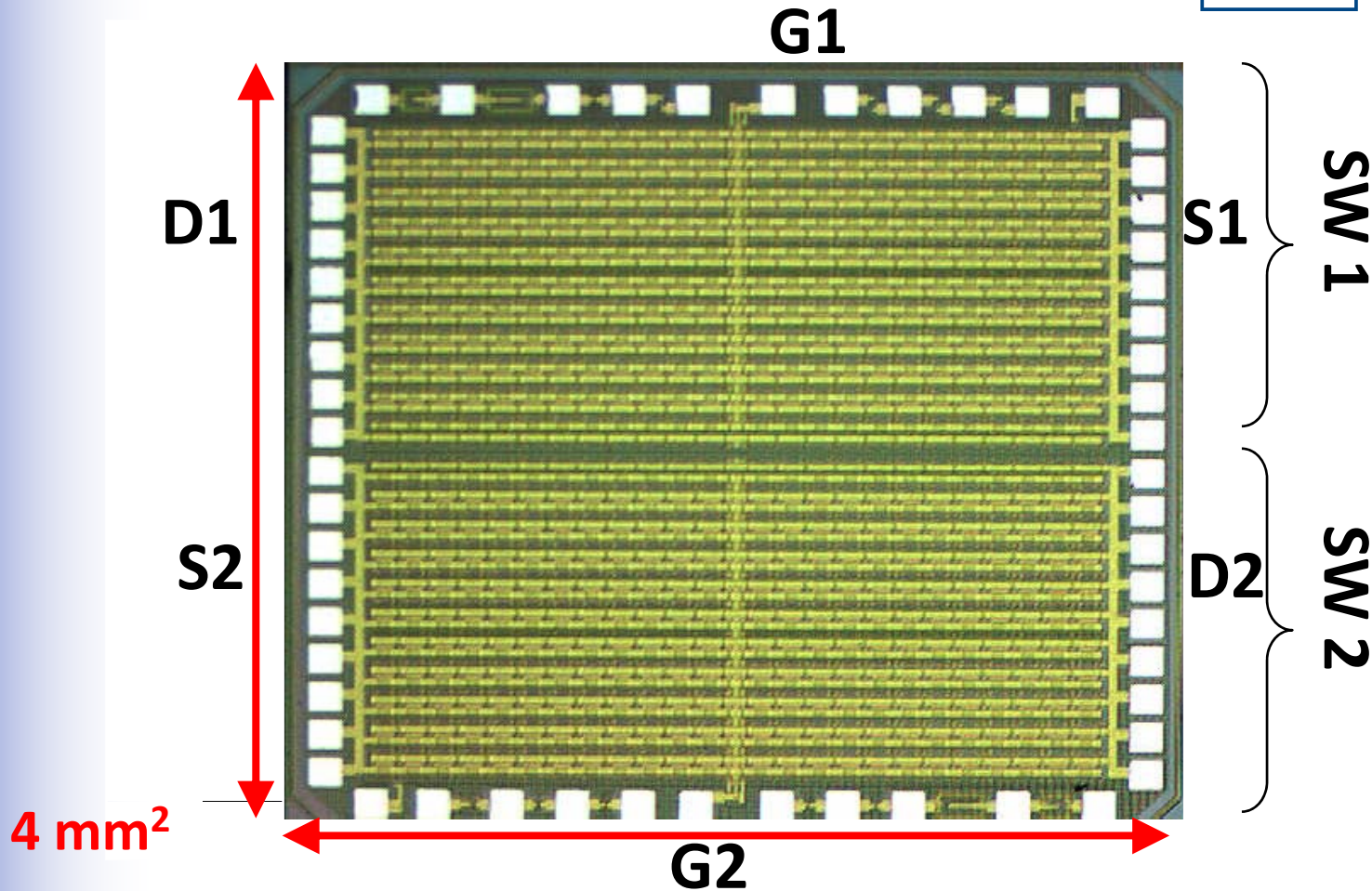
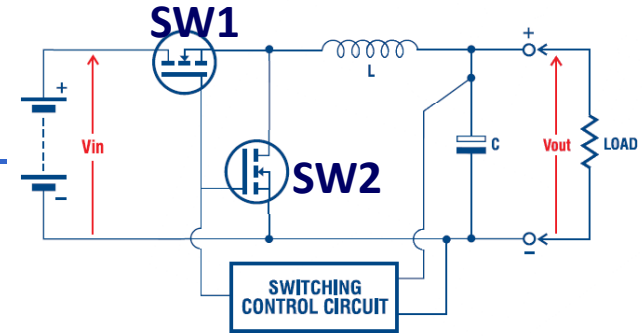
# Efficiency vs $I_{out}$ and $W$

with  $V_{in}=24V$ ,  $V_{out}=2.5V$ ,  $R_{ind}=6m\Omega$  and  $L=700nH$





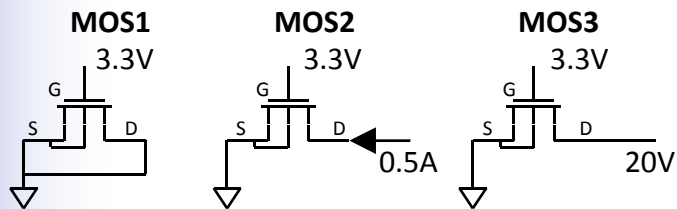
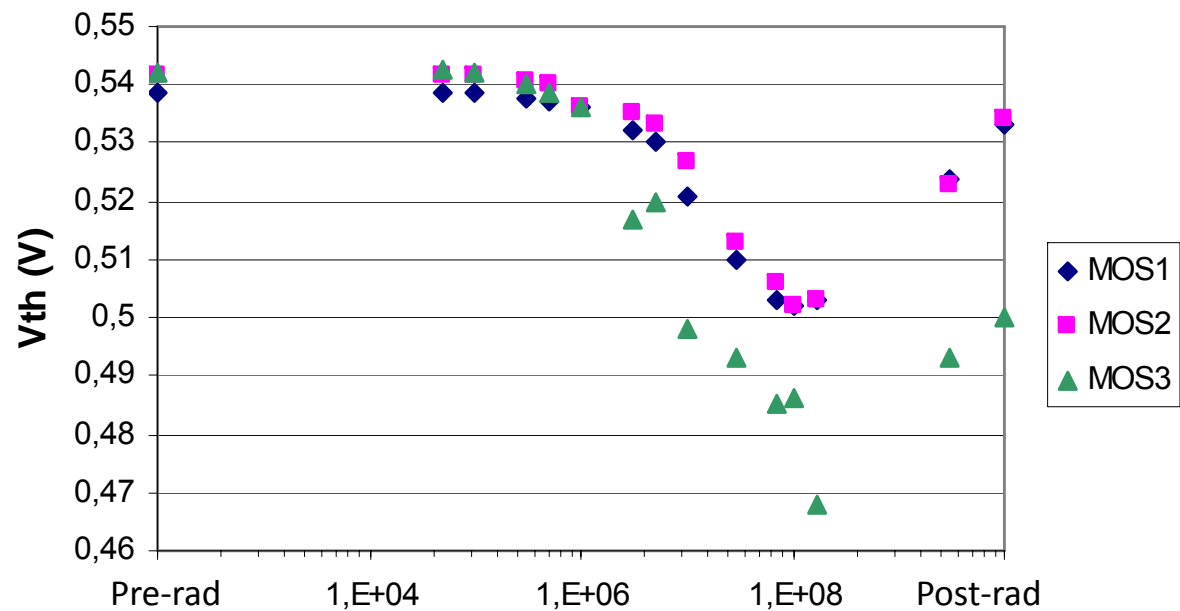
# NMOS design $W=0.1\text{m}$





# NMOS irradiation tests – Threshold Voltage

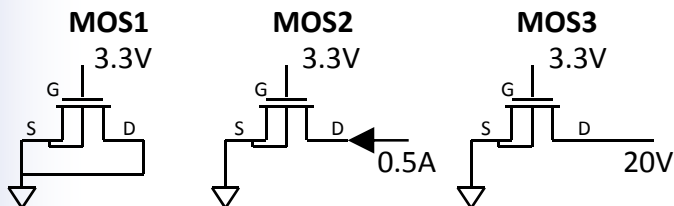
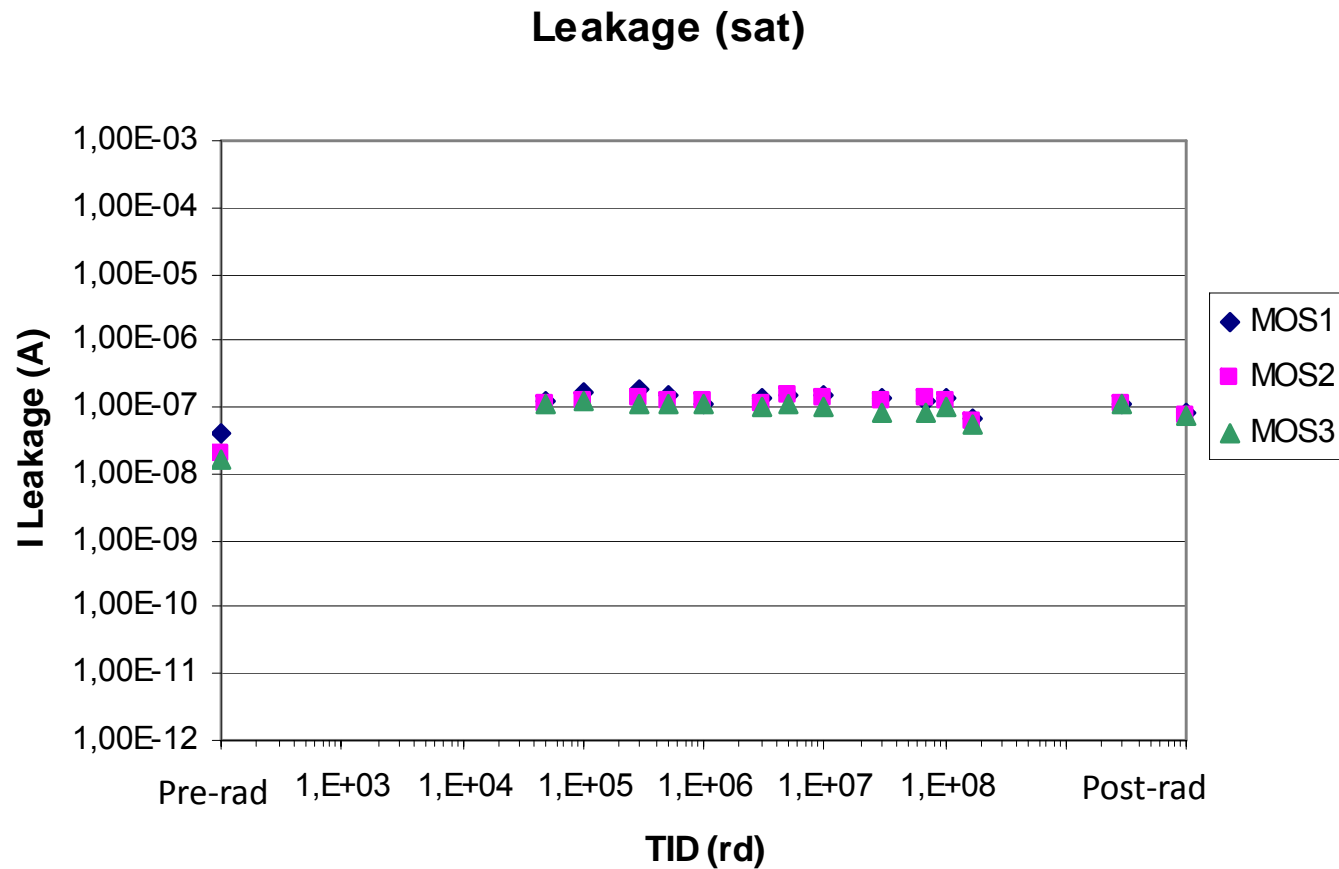
### Vth (linear)



### TID (rd)



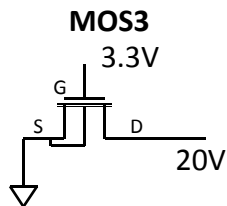
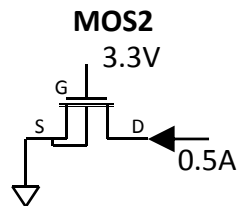
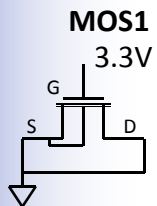
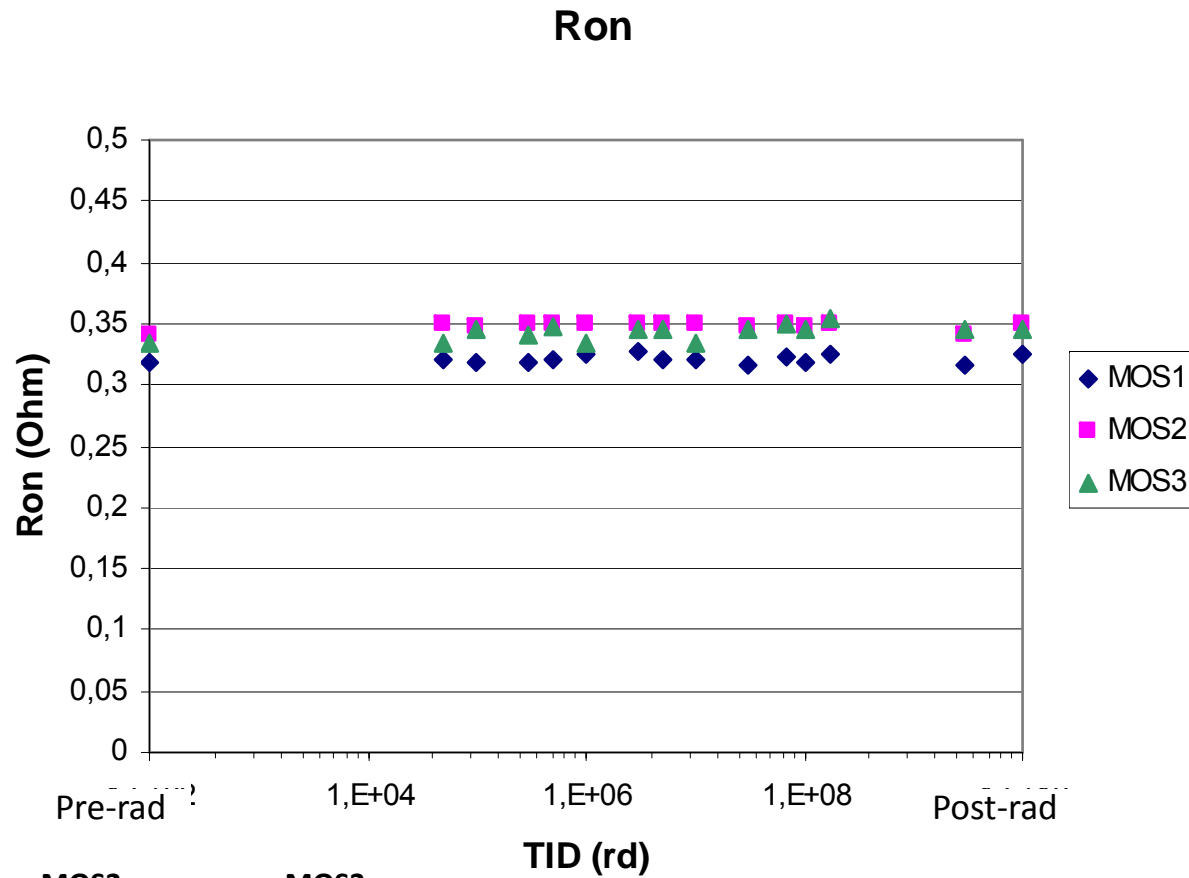
# NMOS irradiation tests – Leakage Current







# NMOS irradiation tests - $R_{on}$





# Conclusions

We have demonstrated that:

1. the technology can be tolerant to TID up to at least 180Mrd and switch transistors of the required size can be integrated
2. Air core inductor can be used in such high DC magnetic field
3. efficiency above 80% is achievable

Evaluation of EMI is in progress

- choosing dedicate architecture and inductor shape
- making measures and trying to standardize the measurement process.